L Number	Hits	Search Text	DB	Time stamp
3	1		USPAT	2004/10/27 13:12
4	1		USPAT	2004/10/27 13:12
5	1		USPAT	2004/10/27 13:13
36	1858	("CF.sub.4" or CF4 or "carbon tetrafluoride") same (vapor or NH3 or "NH.sub.3" or ammonia)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:21
37	67	("CF.sub.4" or CF4 or "carbon tetrafluoride") same (vapor or NH3 or "NH.sub.3" or ammonia) same (residues or redeposit or residual)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:16
38	818	("CF.sub.4" or CF4 or "carbon tetrafluoride") and (plasma with etch$4) and " KHz"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:18
39	209	(MRAM or "magneto resistive random access memory") same (etch$4 or remov$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:17
40	2317	(MRAM or "magneto resistive random access memory")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:17
41	142	((MRAM or "magneto resistive random access memory")) and 438/$.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:18
42	184	(MRAM or "magneto resistive random access memory") and (fluorocarbon or vapor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:18
43	2973	("CF.sub.4" or CF4 or "carbon tetrafluoride") and (plasma with etch$4) and (RF or radiofrequency)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:19
44	5	(("CF.sub.4" or CF4 or "carbon tetrafluoride") and (plasma with etch$4) and (RF or radiofrequency)) and ((MRAM or "magneto resistive random access memory"))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:19
45	2	6355576.pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:19
46	752	("CF.sub.4" or CF4 or "carbon tetrafluoride") same (vapor or NH3 or "NH.sub.3" or ammonia) same (stripp$4 or remov$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:22
47	636	(("CF.sub.4" or CF4 or "carbon tetrafluoride") same (vapor or NH3 or "NH.sub.3" or ammonia) same (stripp$4 or remov$4)) and semi$1conductor$1	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 13:22